



#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

## **Product Summary**

Device	BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D MAX</sub> T <sub>A</sub> = +25°C
N-	001/	$35m\Omega$ @ V <sub>GS</sub> = 4.5V	4.6A
Channel	20V	43mΩ @ V <sub>GS</sub> = 2.5V	4.2A

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

- Load Switch
- Power Management Functions
- Portable Power Adaptors

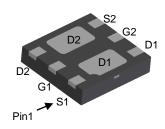
## **Features**

- PCB Footprint of 4mm<sup>2</sup>
- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Maximum Height
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. <a href="https://www.diodes.com/quality/product-definitions/">https://www.diodes.com/quality/product-definitions/</a>

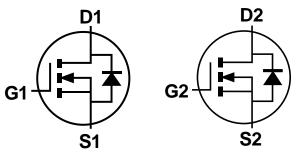
#### **Mechanical Data**

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208@4
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

## U-DFN2020-6 (Type B)



**Bottom View** 



Internal Schematic

#### Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2053UFDB-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMN2053UFDB-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



# **Marking Information**

#### U-DFN2020-6 (Type B)

**H5 YWX**  H5 = Product Type Marking Code YWX = Date Code Marking

Y = Year (ex: 0 = 2020)
W = Week (ex: a = Week 27; z Represents Week 52 and 53)
X = Internal Code (ex: U = Monday)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	9	0	1	2	3	4	5	6	7	8	9	0

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	X	Y	Z



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			VDSS	20	V
Gate-Source Voltage	Vgss	±12	V		
Continuous Drain Current (Note 6) Vcs = 4.5V		T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	lo	4.6 3.7	А
Maximum Continuous Body Diode Forward Current (Note 6	Is	1.1	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	24	Α

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	0.82	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	153	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.14	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	110	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

# Electrical Characteristics N-Channel (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)				•	•	•	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	1.0	μA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	lgss	_	_	±10	μΑ	$V_{GS} = \pm 12V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(TH)	0.4	_	1.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
			23	35		$V_{GS} = 4.5V, I_D = 5A$	
Static Drain-Source On-Resistance	RDS(ON)	_	30	43	mΩ	$V_{GS} = 2.5V, I_{D} = 4A$	
			43	56		Vgs = 1.8V, ID = 2A	
Diode Forward Voltage	VsD	_	0.7	1.2	V	Vgs = 0V, Is = 1A	
DYNAMIC CHARACTERISTICS (Note 8)						•	
Input Capacitance	C <sub>iss</sub>	_	369	_		101/11/ 01/	
Output Capacitance	Coss	_	54	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	32	_			
Gate Resistance	Rg	_	4.1	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	3.6	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	7.7	_	nC	V 40V I CA	
Gate-Source Charge	Qgs	_	0.4	_	nc nc	$V_{DS} = 10V, I_{D} = 6A$	
Gate-Drain Charge	Qgd	_	1.0	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	2.6	_			
Turn-On Rise Time	t <sub>R</sub>	_	3.0	_		$V_{DS} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	12.5	_	ns	$R_g = 6\Omega$ , $R_L = 10\Omega$ , $I_D = 6A$	
Turn-Off Fall Time	t <sub>F</sub>	_	3.6	_			
Reverse Recovery Time	trr	_	6.0	_	ns	I <sub>F</sub> = 1A, di/dt = 100A/μs	
Reverse Recovery Charge	Q <sub>RR</sub>		0.9	_	nC	I <sub>F</sub> = 1A, di/dt = 100A/μs	

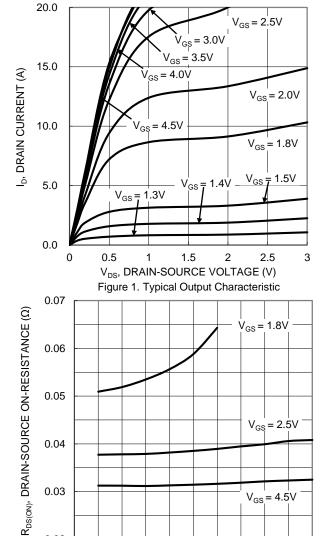
5. Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.

<sup>6.</sup> Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.

<sup>8.</sup> Guaranteed by design. Not subject to product testing.

## DMN2053UFDB





I<sub>D</sub>, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

5 6 7 8

4

10

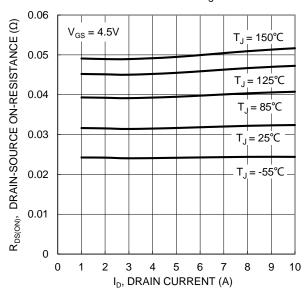


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

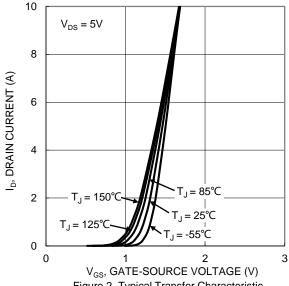


Figure 2. Typical Transfer Characteristic

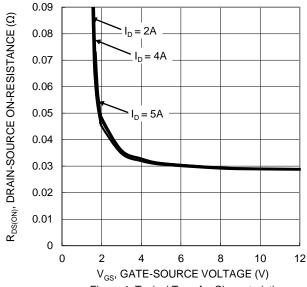


Figure 4. Typical Transfer Characteristic

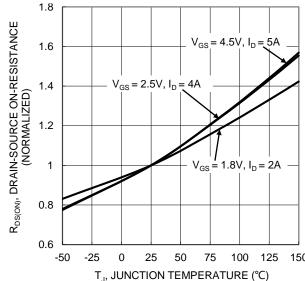


Figure 6. On-Resistance Variation with Junction Temperature

0.02

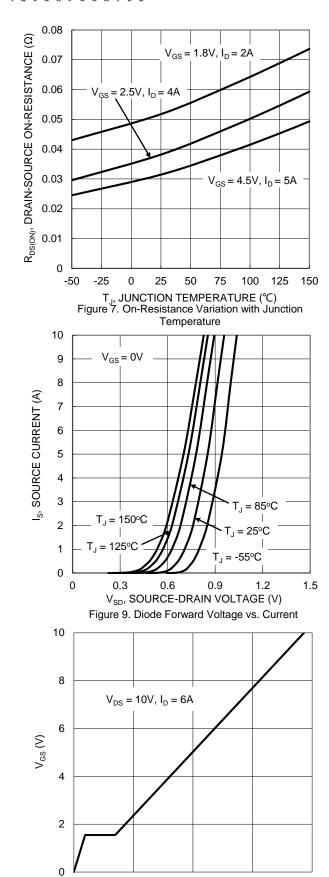
0

1

2 3



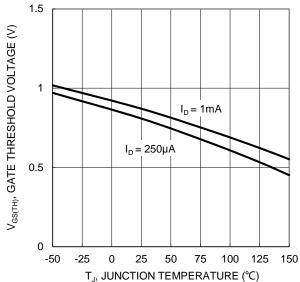




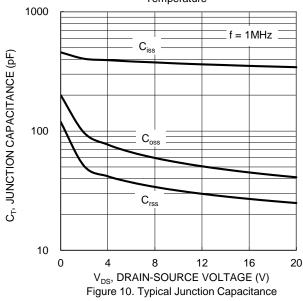
 $Q_g$  (nC) Figure 11. Gate Charge

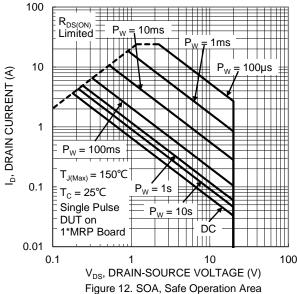
4

6



 $\rm T_{\rm J},$  JUNCTION TEMPERATURE (°C) Figure 8. Gate Threshold Variation vs. Junction Temperature





0

2

8



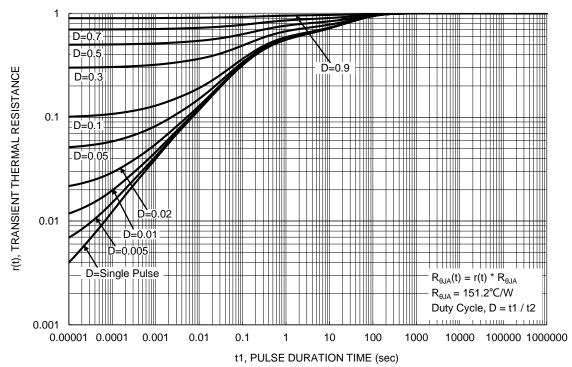


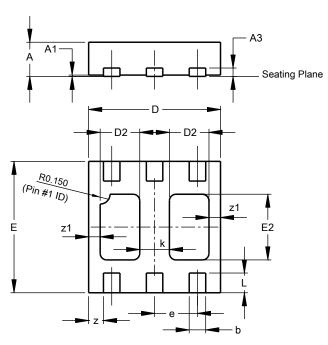
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2020-6 (Type B)

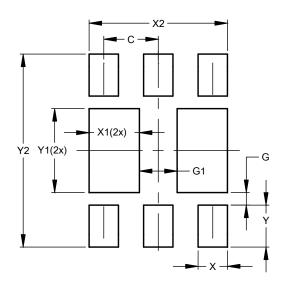


U-DFN2020-6 Type B						
Dim	Min	<u> </u>				
Α	0.545	0.605	<b>Typ</b> 0.575			
A1	0.00	0.05	0.02			
A3	_	_	0.13			
b	0.20	0.30	0.25			
D	1.95	2.075	2.00			
D2	0.50	0.70	0.60			
е	-	_	0.65			
E	1.95	2.075	2.00			
E2	0.90	1.10	1.00			
k	_	_	0.45			
L	0.25	0.35	0.30			
Z	_	_	0.225			
z1	_	_	0.175			
All	Dimens	ions in	mm			

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2020-6 (Type B)



Dimensions	Value (in mm)
С	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300



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